ABSTRACT OF THE DISCLOSURE

The reliability of a GOLD structure TFT depends on an impurity concentration in its gate-overlapped region. Thus, it is an object of the present invention to obtain a resistance distribution corresponding to a tapered shape of a gate electrode in a gate-overlapped region. According to the present invention, plural TEGs are manufactured as Lov resistance monitors in which mask alignment is misaligned with several μm interval to perform a resistance measurement on each of the TEGs. Consequently, a resistance distribution corresponding to a tapered shape can be obtained in a channel forming region, a gate-overlapped region and a source/drain region.